

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jennifer STONE-SUNDBERG, et al.

Title: SPINEL BOULES, WAFERS, AND METHODS FOR FABRICATING
SAME

Application No.: NEW APPLICATION Filed: HEREWITH

Atty. Docket No.: 1035-BI4281

MS PATENT APPLICATION
COMMISSIONER FOR PATENTS
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings the patents, publications, applications or other information identified in the attached:

- ☒ Form(s) PTO/SB/08A and/or PTO/SB/08B
☐ Other: n/a

to the Examiner's attention in the above-identified application. These references were cited in parent Application No. , filed . Accordingly, in accordance with C.F.R. §1.98(d), copies of the references are not being supplied herewith. Citation of such information shall not be construed as:

1. an admission that the information necessarily is, or corresponds to, prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described below; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance, such as through (i) an English language abstract, (ii) an English language equivalent application, (iii) reference to discussion in the application, or (iv) if cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

EXPRESS MAIL MAILING LABEL NUMBER: <u>EV 335894775 US</u>
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STATEMENT UNDER 37 C.F.R. § 1.704(d)

If the above-identified application is an original application filed on or after May 29, 2000:

- ☐ each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in § 1.56(c) more than thirty days prior to the filing of this Information Disclosure Statement.

FEES DUE

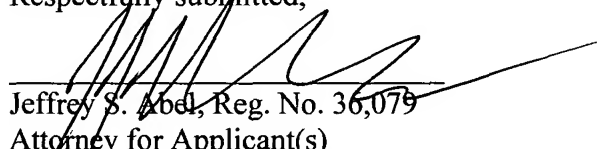
This Information Disclosure Statement is being filed:

- ☒ within three months of the filing date of a national application or within three months of entry of the national stage as set forth in § 1.491 in an international application. Therefore, no fee is required.
- ☐ before the mailing date of a first Office action on the merits or before the mailing date of a first Office action after the filing of a request for continued examination under § 1.114. Therefore, no fee is believed required.
- ☐ after the period specified in § 1.97(c), but on or before payment of the issue fee. Accordingly, the fee set forth in § 1.17(p) is required and provided as shown on the attached Fee Transmittal.

If however, this Information Disclosure Statement is determined by the USPTO to be filed after the period specified in § 1.97(b), the undersigned hereby authorizes the Commissioner to charge the fee set forth in § 1.17(p) as shown on the attached Fee Transmittal.

8/23/03
Date

Respectfully submitted,


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Substitute for form 1449/PTO

Complete if Known
Application Number **NEW APPLICATION**
Filing Date **HEREWITH**
First Named Inventor **Jennifer Ston -Sundberg**
Attorney Docket Number **1035-BI4281**

Sheet 1 of 3
(use as many sheets as necessary)

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. 1	U.S. Patent Document Number	Kind Code 2 (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	3,655,439		SEITER	04/11/1972	
	AB	3,658,586		WANG	04/25/1972	
	AC	3,796,597		V.R. PORTER, et al.	03/12/1974	
	AD	4,177,321		NISHIZAWA	12/04/1979	
	AE	5,741,724		RAMDANI, et al.	04/21/1998	
	AF	5,850,410		KURAMATA	12/15/1998	
	AG	5,530,267		BRANDLE, JR., et al.	06/25/1996	
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	AI	3,883,313		CULLEN, et al.	05/13/1975	
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	AL	EP	0 148 656	A1	AUZEL, et al.	11/16/1984		<input type="checkbox"/>
	AM							<input type="checkbox"/>

PUBLICATIONS

Examiner Initials *	Cite No. 1	Title of Publication	Date of Publication of Cited Document MM-DD-YYYY
	AV	YUMASHEV K.V., et al., "Co ²⁺ -doped spinels saturable absorber Q-switches for 1.3-1.6 μ m solid state lasers", OSA TRENDS IN OPTICS AND PHOTONICS. ADVANCED SOLID STATE LASERS., Vol. 34, pp. 236-239, 2000. XP008017966	
	AW	YUMASHEV, K.V., et al., "Passive Q-switching of 1.34- μ m neodymium laser using Co ²⁺ :LiGa ₅ O ₈ and Co ²⁺ :MgAl ₂ O ₄ ", CONFERENCE DIGEST, 2000, 1 page. XP002242959	
	AX	OKTYABRSKY, S., et al., "Crystal structure and defects in nitrogen-deficient GaN", MRS Internet J. Nitride Semicond. Res, G6.43, pp. 1-6, 1999.	
	AY	KLEBER, W., et al., "Zur epitaxie von galliumnitrid auf nichtstochiometrischem spinell im system GaCl/NH ₃ /He", CRYSTAL RESEARCH AND TECHNOLOGY, Vol. 10, No. 7, pp. 747-758, 1975. (English Abstract)	
	AZ	SEIFERT, A., "Nachweis von stapelfehlern in GaN-epitaxieschichten mittels elektronenbeugung", CRYSTAL RESEARCH AND TECHNOLOGY, Vol. 10, No. 7, pp. 741-746, 1975. (English Abstract)	
Examiner Signature			Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Unique citation designation number. 2 See attached Kinds of U.S. Patent Documents. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

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	AAA	KULESHOV, N.V., et al. "Co-doped spinels: promising materials for solid state lasers", LONGER WAVELENGTH LASERS AND APPLICATIONS, Vol. 2138, pp. 175-182, 1994. XP008017848	
	AAB	KULESHOV, N.V., et al., "Absorption and luminescence of tetrahedral Co ²⁺ ion in MgAl ₂ O ₄ , Vol. 55, no. 5-6, pp. 265-269, 1993. XP008017849	
	AAC	NIKISHIN, S.A., et al., "Gas source molecular beam epitaxy of GaN with hydrazine on spinel substrates", APPLIED PHYSICS LETTERS, Vol. 72, No. 19, pp. 2361-2363, 1998. XP000755963	
	AAD	HAISMA, et al., "Lattice constant adaptable crystallographics", JOURNAL OF CRYSTAL GROWTH, Vol. 102, pp. 979-993, 1990. XP002250056	
	AAE	TAMURA, K., et al., "Epitaxial growth of ZnO film on lattice-matched ScAlMgO ₄ (0001) substrates", JOURNAL OF CRYSTAL GROWTH, Vol. 214-215, pp. 59-62, 2000. XP004200964	
	AAF	WYON, et al., "Czochralski growth and optical properties of magnesium-aluminum spinel doped with nickel", JOURNAL OF CRYSTAL GROWTH, Vol. 79, pp. 710-713, 1986. XP002250057	
	AAG	TSUCHIYA, T., et al. "Epitaxial growth of InN films on MgAl ₂ O ₄ (1 1 1) substrates", JOURNAL OF CRYSTAL GROWTH, Vol. 220, pp. 185-190, 2000.	
	AAH	KURAMATA, Akito, et al., "High-quality GaN epitaxial layer grown by metalorganic vapor phase epitaxy on (111) MgAl ₂ O ₄ substrate", APPL. PHYS. LETT., Vol. 67, No. 17, pp. 2521-2523, 1995.	
	AAI	MITCHELL, T., "Dislocations and Mechanical Properties of MgO- MgAl ₂ O ₃ spinel single crystals", J. AM. CERAM. SOC., Vol. 82, No. 12, pp. 3305-3316, 1999.	
	AAJ	HELLMAN, E., "Exotic and Mundane substrates for gallium nitride heteroepitaxy", BELL LABORATORIES, THC2, Murray Hill, NJ.	
	AAK	KRUGER, M.B., et al., "Equation of state of MgAl ₂ O ₄ spinel to 65 GPa", THE AMERICAN PHYSICAL SOCIETY, Vol. 56, No. 1, pp. 1-4, 1997.	
	AAL	KURAMATA, A., et al., "Properties of GaN epitaxial layer grown on (111) MgAl ₂ O ₄ substrate", SOLID-STATE ELECTRONICS, Vol. 41, No. 2, pp. 251-254, 1997.	
	AAM	GRITSYNA, V., et al., "Structure and Electronic states of defects in spinel of different compositions MgO · n MgAl ₂ O ₃ · Me", J. AM. CERAM. SOC. Vol. 82, No. 1, pp. 3365-3373, 1999.	
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	BA	6,533,874	B1	VAUDO, et al.	03/18/2003	
	BB	4,627,064		AUZEL, et al.	12/02/1986	
	BC	4,000,977		FALCKENBERG	01/04/1977	
	BD					
	BE					
	BF					
	BG					
	BH					
	BI					
	BJ					
	BK					

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	BL						<input type="checkbox"/>
	BM						<input type="checkbox"/>

PUBLICATIONS

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	BW	OHSATO, H., et al., "Epitaxial orientation and a growth model of (0 0 • 1) GaN thin film on (1 1 1) spinel substrate", JOURNAL OF CRYSTAL GROWTH, Vol. 189/190, pp. 202-207, 1998.	
	BX	YANG, H. -F., et al., "Microstructure evolution of GaN buffer layer on MgAl ₂ O ₄ substrate", JOURNAL OF CRYSTAL GROWTH, Vol. 193, pp. 478-483, 1998.	
	BY	DUAN, S., et al., "MOVPE growth of GaN and LED on (1 1 1) MgAl ₂ O ₄ ", JOURNAL OF CRYSTAL GROWTH, Vol. 189/190, pp. 197-201, 1998.	
	BZ	SHELDON, R., et al., "Cation Disorder and Vacancy Distribution in Nonstoichiometric Magnesium Aluminate Spinel, MgO • Al ₂ O ₃ ", J. AM. CERAM. SOC., Vol. 82, No. 12, pp. 3293-3298, 1999.	
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